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In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A method for depositing in particular crystalline active layers on in particular at least one crystalline substrates substrate from gaseous starting substances, which are introduced, in particular together with a carrier gas, into the process chamber of a reactor, where, depending on process parameters determined in preliminary tests, such as in particular selected from the group consisting of substrate temperature, process chamber pressure, mass flow of the starting substances introduced into the process chamber, and total mass flow, and combinations thereof, in particular after prior pyrolytic decomposition, they the starting substances are deposited on the substrate and form an active layer, the layer layer having properties of which selected from the group consisting of -such as in particular stoichiometry, doping, morphology, temperature, growth rate, and combinations thereof or the like, are determined from surface measurements or measured without contact by means of sensors acting in the process chamber, characterized in that, in addition to the set of process parameters which contains contain the process parameters which lead to the desired layer properties, calibration parameters are also determined in the preliminary tests, by the deviations in the layer properties when individual process parameters are varied being determined and the corresponding deviation being placed into a relationship with the process parameter variation, and by, in the production run, prior to the deposition of the active layer, at least one calibration layer, the layer properties of which are measured or determined, being deposited in the same production run, deviation values being formed by placing these properties in a relationship to the desired layer properties, and by one or more process parameters being altered in accordance with the calibration parameters for deposition of the active layer as a function of the magnitude of the deviation values.

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- 2. (Currently amended) A-The method according to Claim 1, characterized in that the method is an MOCVD method.
- 3. (Currently amended) A-<u>The</u> method according to claim 1, characterized in that the wherein the -process parameters <u>further comprise</u> also encompasses the source temperature of the liquid MO-MOCVD sources.
- 4. (Currently amended) A-<u>The</u> method according to claim 1, characterized in that the mass flows are measured and controlled using mass flow controllers.
- 5. (Currently amended) A-The method according to claim 1, characterized in that the starting substances also comprise one or more dopants, and the dopant concentration is also determined as a layer property.
- 6. (Currently amended) A-<u>The</u> method according to claim 1, characterized in that the stress in the layer is also determined as a layer property.
- 7. (Currently amended) A-<u>The</u> method according to claim 1, characterized in that the sensor is a reflection anisotropy spectroscope (RAS) or an ellipsometer.
- 8. (Currently amended) A-<u>The</u> method according to claim 1, characterized in that the sensor for the temperature measurement is a thermocouple or an optical sensor, for example a pyrometer.
- 9. (Currently amended) A-<u>The</u> method according to claim 1, characterized in that the in situ measurement is carried out using X-ray diffraction, electron diffraction (REED) or IR reflectometry.
- 10. (Currently amended) A-<u>The</u> method according to claim 1, characterized in that the calibration layers comprise a multilayer structure.

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- 11. (Currently amended) A-<u>The</u> method according to claim 1, characterized in that the layers in the calibration layer sequence have different energy gaps.
- 12. (Currently amended) A-<u>The</u> method according to claim 1, characterized in that the calibration layers have different growth rates.
- 13. (Currently amended) A-<u>The</u> method according to claim 1, characterized in that the production run, in the event of the desired layer properties not being maintained, is interrupted and/or deposits a covering layer on the layer.
- 14. (Canceled)
- 15. (Canceled)
- 16. (New) The method according to claim 1, wherein the sensor for the temperature measurement is a pyrometer.